

Silicon Epitaxial Planar Transistor

2SC5344

FEATURES

- Excellent h_{FE} linearity
- Power dissipation.

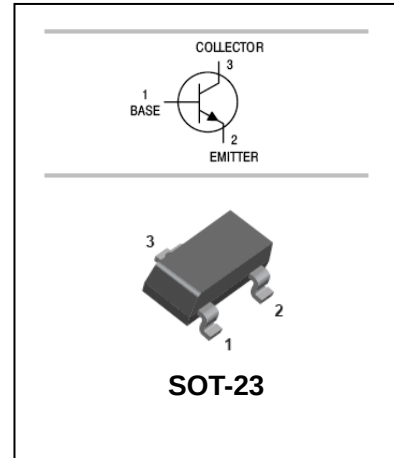


APPLICATIONS

- General small signal amplifier.

ORDERING INFORMATION

Type No.	Marking	Package Code
2SC5344	FAO/FAY	SOT-23



MAXIMUM RATING @ $T_a=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	35	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	800	mA
P_C	Collector Dissipation	200	mW
T_j, T_{stg}	Junction and Storage Temperature	-55~150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS @ $T_a=25^{\circ}\text{C}$ unless otherwise specified

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Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=35V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=1V, I_C=100mA$	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$			0.5	V
Transition frequency	f_T	$V_{CE}=5V, I_C=10mA$	120			MHz
Output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1kHz$			13	pF

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	100-200	160-320
Marking	FAO	FAY

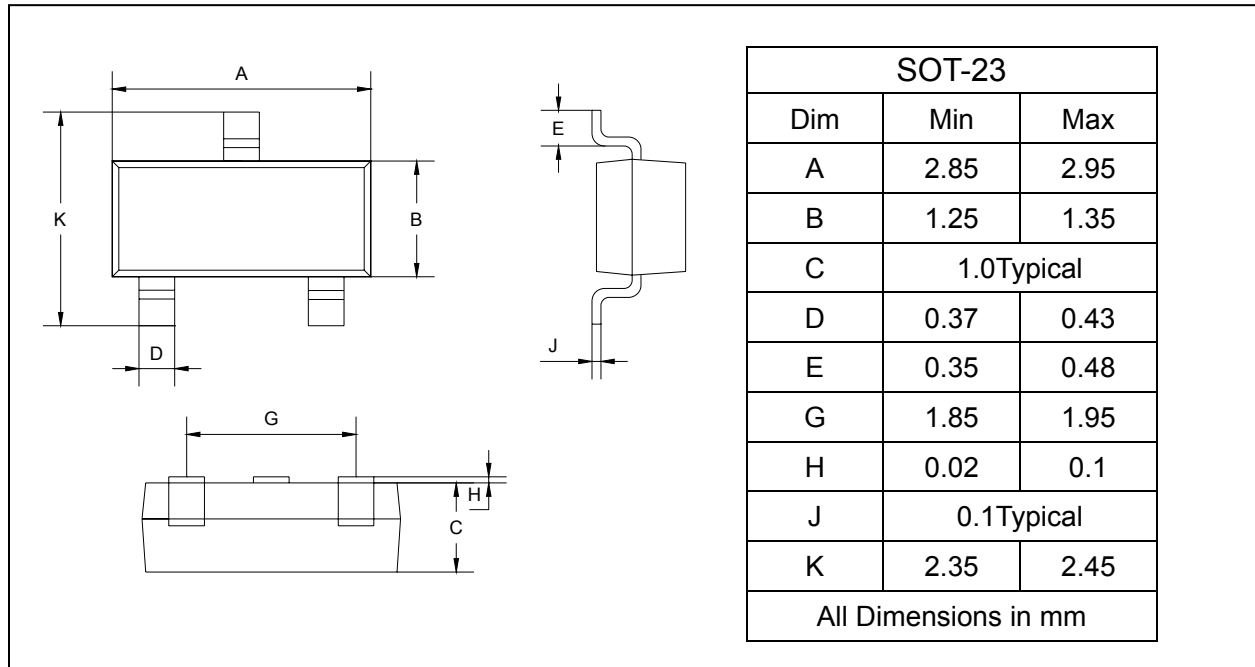
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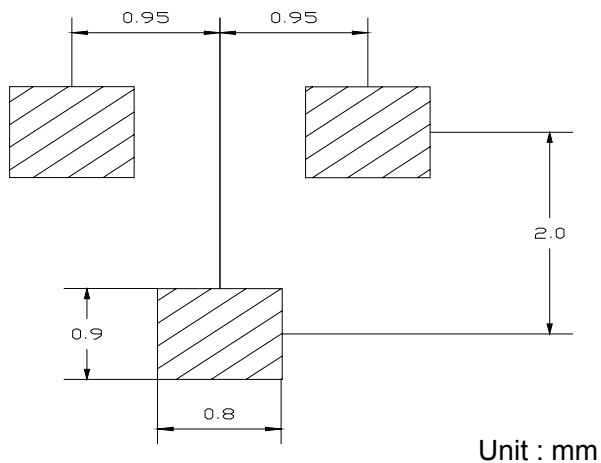
PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
2SC5344	SOT-23	3000/Tape&Reel